# mail

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## **Digital Transistors (BRT)** R1 = 47 k $\Omega$ , R2 = $\infty$ k $\Omega$

## NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ )

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	6	Vdc

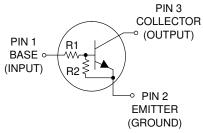
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

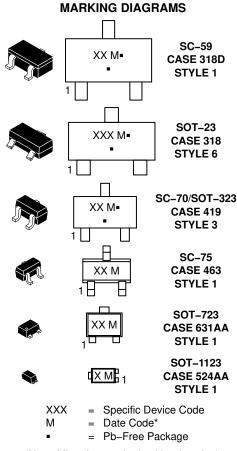


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(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

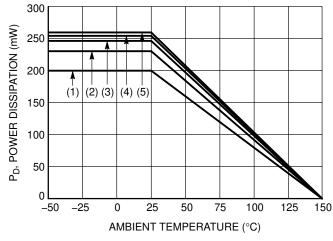
See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

#### Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2240T1G, SMUN2240T1G	8T	SC–59 (Pb–Free)	3000 / Tape & Reel
MMUN2240LT1G	AA4	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5240T1G	AR	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC144TET1G	7T	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC144TM3T5G, NSVDTC144TM3T5G	8T	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC144TF3T5G	K (180°)	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*  $(xx^{\circ})$  = Degree rotation in the clockwise direction.



SC-75 and SC-70/SOT323; Minimum Pad
SC-59; Minimum Pad
SOT-23; Minimum Pad
SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
SOT-723; Minimum Pad

Figure 1. Derating Curve

#### **Table 2. THERMAL CHARACTERISTICS**

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2240)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1)	P <sub>D</sub>	230 338 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 1) (Note 2)	$R_{\theta JA}$	2.7 540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ ext{ heta}JL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2240L)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ ext{ heta}JL}$	174 208	°C/W
Junction and Storage Temperature Range		TJ, T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5240)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\theta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ ext{ heta}JL}$	280 332	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTC144TE)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temperature Range		TJ, T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTC144TM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\thetaJA}$	480 205	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

2. FR-4 @ 1.0 x 1.0 Inch Pad. 3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air. 4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

#### **Table 2. THERMAL CHARACTERISTICS**

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC144TF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{\theta JL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

1. FR-4 @ Minimum Pad.

2. FR-4 @ 1.0 x 1.0 Inch Pad.

FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

#### Table 3. ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	-	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	_	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0 \text{ V}, I_C = 0$ )	I <sub>EBO</sub>	_	-	0.2	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V <sub>(BR)CEO</sub>	50	-	_	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) ( $I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$ )	h <sub>FE</sub>	120	300	-	
Collector–Emitter Saturation Voltage (Note 5) $(I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA})$	V <sub>CE(sat)</sub>	_	-	0.25	Vdc
Input Voltage (off) (V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 $\mu$ A)	V <sub>i(off)</sub>	-	0.6	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.3 \text{ V}, I_{C} = 10 \text{ mA}$ )	V <sub>i(on)</sub>	4.0	2.6	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 3.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC}$ = 5.0 V, $V_B$ = 0.25 V, $R_L$ = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.

TYPICAL CHARACTERISTICS - MUN2240, MMUN2240L, MUN5240, DTC144TE, DTC144TM3

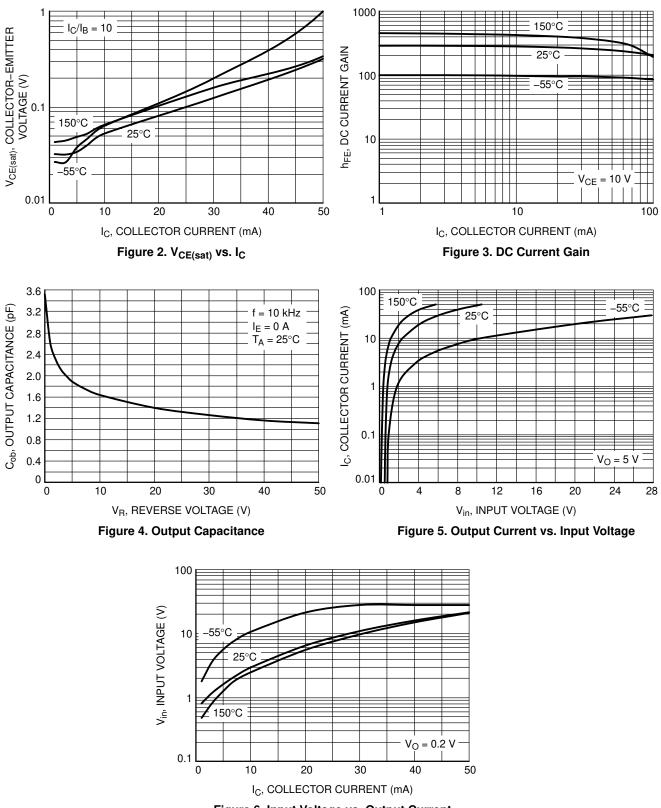
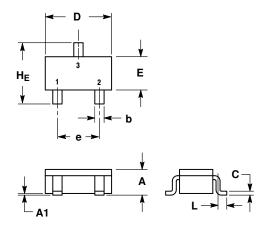


Figure 6. Input Voltage vs. Output Current

## PACKAGE DIMENSIONS

**SC-59** CASE 318D-04 ISSUE H

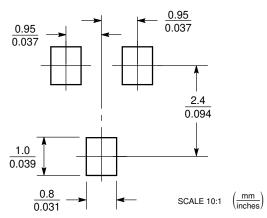


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

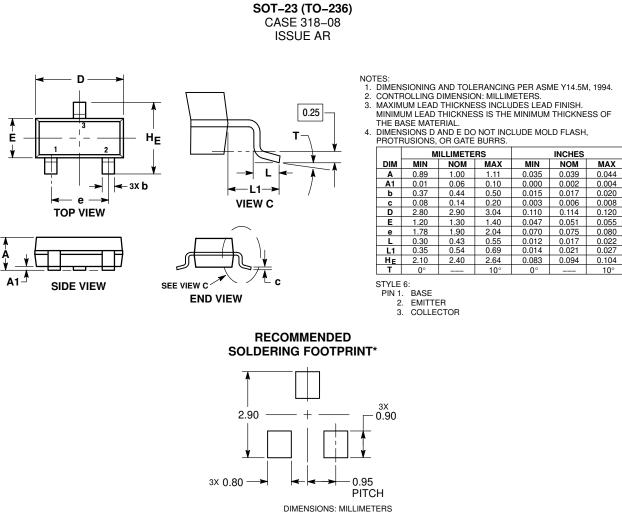
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
Е	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

#### SOLDERING FOOTPRINT\*

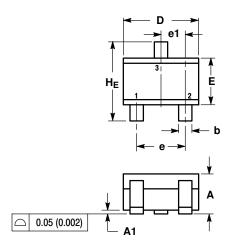


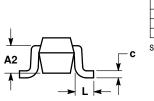
#### PACKAGE DIMENSIONS



## PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 **ISSUE N** 





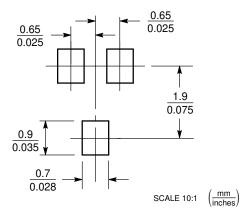
NOTES: DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF		0.028 REF			
σ	0.30	0.35	0.40	0.012	0.014	0.016	
c	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
Е	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC			0.026 BSC			
Г	0.20	0.38	0.56	0.008	0.015	0.022	
ΗE	2.00	2.10	2.40	0.079	0.083	0.095	



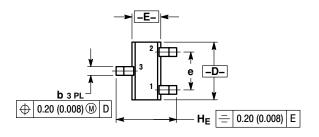
STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR

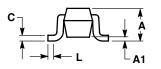
SOLDERING FOOTPRINT\*



## PACKAGE DIMENSIONS

SC-75/SOT-416 CASE 463 **ISSUE F** 



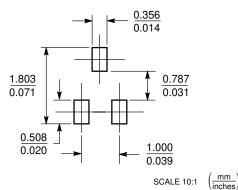


NOTES: DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.

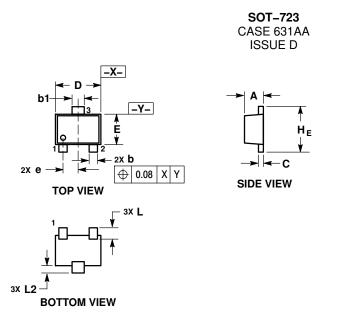
	MIL	LIMETE	INCHES					
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.70	0.80	0.90	0.027	0.031	0.035		
A1	0.00	0.05	0.10	0.000	0.002	0.004		
b	0.15	0.20	0.30	0.006	0.008	0.012		
С	0.10	0.15	0.25	0.004	0.006	0.010		
D	1.55	1.60	1.65	0.059	0.063	0.067		
E	0.70	0.80	0.90	0.027	0.031	0.035		
е	1.00 BSC			0.04 BSC				
L	0.10	0.15	0.20	0.004	0.006	0.008		
HE	1.50	1.60	1.70	0.061	0.063	0.065		

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

**SOLDERING FOOTPRINT\*** 



### PACKAGE DIMENSIONS



NOTES: I. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MILLIMETERS DIM 
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 0.50
 0.55

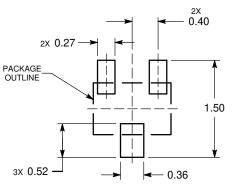
 0.15
 0.21
 0.27
 Α b 
 0.25
 0.31
 0.37

 0.07
 0.12
 0.17

 1.15
 1.20
 1.25
 b1 C D 0.75 0.80 0.85 Е e H⊧ 0.40 BS0 1.15 1.20 1.25 0.29 REF L L2 0.15 0.20 0.25 STYLE 1:

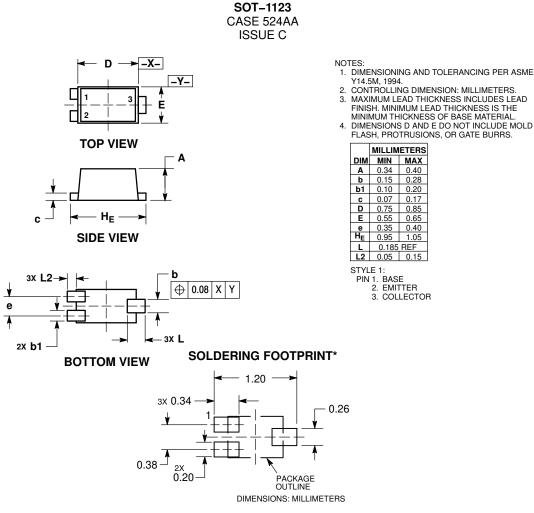
PIN 1. BASE 2. EMITTER 3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

#### PACKAGE DIMENSIONS



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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